Dual Bus Buffer with 3-state Output

HITACHI

ADE-205-348 (Z) 1st. Edition May 2000

Description

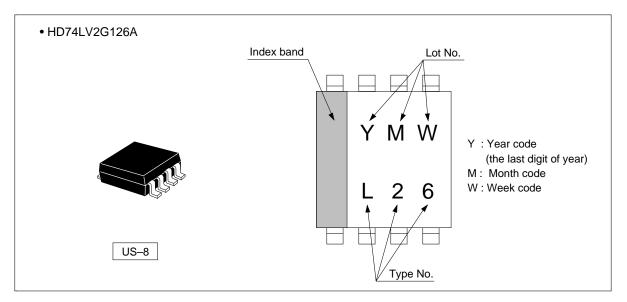
The HD74LV2G126A has dual bus buffer with 3-state output in a 8 pin package. Output is disabled when the associated output enable (OE) input is low. To ensure the high impedance state during power up or power down, OE should be connected to $V_{\rm CC}$ through a pull-down resistor; the minimum value of the resistor is determined by the current souring capability of the driver. Low voltage and high speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

- The basic gate function is lined up as hitachi uni logic series.
- Supplied on emboss taping for high speed automatic mounting.
- Electrical characteristics equivalent to the HD74LV126A Supply voltage range: 1.65 to 5.5 V
 Operating temperature range: -40 to +85°C
- All inputs V_{IH} (Max.) = 5.5 V (@ V_{CC} = 0 V to 5.5 V) All outputs V_{O} (Max.) = 5.5 V (@ V_{CC} = 0 V)
- Output current ± 6 mA (@V_{CC} = 3.0 V to 3.6 V), ± 12 mA (@V_{CC} = 4.5 V to 5.5 V)
- All the logical input has hysteresis voltage for the slow transition.



Outline and Article Indication

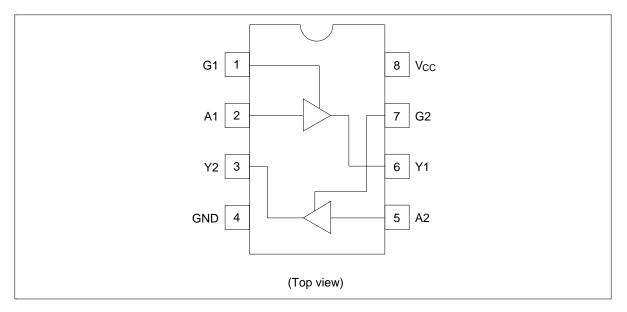


Function Table

Inputs		Output Y				
OE	A	_				
Н	Н	Н				
Н	L	L				
L	X	Z				

H : High level
L : Low level
X : Immaterial
Z : High impedance

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage	V _{cc}	-0.5 to 7.0	V	
Input voltage	V _{IN}	-0.5 to 7.0	V	
Output voltage	V _{out}	-0.5 to V_{cc} + 0.5	V	Output : H or L
		-0.5 to 7.0		V _{cc} : OFF or Output : Z
Input diode current	I _{IK}	-20	mA	
Output diode current	I _{ok}	±50	mA	"
Output current	I _{OUT}	±25	mA	
V _{cc} , GND current	I _{CC} or I _{GND}	±50	mA	
Power dissipation	P _T	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Recommended Operating Conditions

Item	Symbol	Ratings	Unit
Supply voltage	V _{cc}	1.65 to 5.5	V
Input voltage	V _{IN}	0 to 5.5	V
Output voltage	V_{OUT}	0 to V _{cc}	V
Operating temperature	T_{opr}	-40 to +85	°C
Input rise / fall time	t _r , t _f	0 to 300 (V _{CC} = 1.65 to 1.95 V)	ns
		0 to 200 ($V_{CC} = 2.3$ to 2.7 V)	
		0 to 100 ($V_{CC} = 3.0$ to 3.6 V)	_
		0 to 20 (V _{CC} = 4.5 to 5.5 V)	

Electrical Characteristic

• $Ta = -40 \text{ to } 85^{\circ}C$

Item	Symbol	V _{cc} (V) *	Min	Тур	Max	Unit	Test condition
Input voltage	V _{IH}	1.65 to 1.95	V _{cc} ×0.75	_	_	V	
		2.3 to 2.7	$V_{cc} \times 0.7$	_	_	_	
		3.0 to 3.6	V _{cc} ×0.7	_	_	_	
		4.5 to 5.5	$V_{cc} \times 0.7$	_	_	_	
	V _{IL}	1.65 to 1.95	_	_	V _{cc} ×0.25		
		2.3 to 2.7	_	_	$V_{cc}\!\! imes\!0.3$		
		3.0 to 3.6	_	_	V_{cc} \times 0.3	_	
		4.5 to 5.5	_	_	V _{cc} ×0.3		
Hysteresis voltage	V_{H}	1.8	_	0.25	_	V	$V_T^+ - V_T^-$
		2.5	_	0.30	_	_	
		3.3	_	0.35			
		5.0	_	0.45			
Output voltage	V_{OH}	Min to Max	V _{cc} -0.1	_	_	V	$I_{OH} = -50 \ \mu A$
		1.65	1.4	_			$I_{OH} = -1 \text{ mA}$
		2.3	2.0	_	_	_	$I_{OH} = -2 \text{ mA}$
		3.0	2.48	_	_	_	I _{OH} = -6 mA
		4.5	3.8	_			I _{OH} = -12 mA
	V _{OL}	Min to Max	_	_	0.1		$I_{OL} = 50 \mu A$
		1.65	_	_	0.3		I _{OL} = 1 mA
		2.3	_	_	0.4		$I_{OL} = 2 \text{ mA}$
		3.0	_	_	0.44		$I_{OL} = 6 \text{ mA}$
		4.5	_	_	0.55	_	I _{OL} = 12 mA
Input current	I _{IN}	0 to 5.5	_	_	±1	μΑ	$V_{IN} = 5.5 \text{ V or GND}$
Off state output current	I _{oz}	5.5	_	_	±5	μΑ	$V_o = V_{CC}$ or GND
Quiescent supply current	I _{cc}	5.5			10	μА	$V_{IN} = V_{CC}$ or GND, $I_{O} = 0$
Output leakage current	I _{OFF}	0	_	_	5	μΑ	V _o = 5.5 V
Input capacitance	C _{IN}	3.3		3.0	_	pF	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Switching Characteristics

• $V_{CC} = 1.8 \pm 0.15 \text{ V}$

Item	Symbol	$T_a = 25^{\circ}C$		$T_a = -40 \text{ to } 85^{\circ}\text{C}$		Unit	Test	FROM	то	
		Min	Тур	Max	Min	Max	_	Conditions	(Input)	(Output)
Propagation	t _{PLH}	_	13.5	23.5	1.0	26.0	ns	C _L = 15 pF	Α	Υ
delay time	$t_{\tiny PHL}$	_	19.0	33.0	1.0	36.0	_	$C_L = 50 pF$	_	
Enable time	t _{zH}	_	13.7	26.5	1.0	29.0	ns	C _L = 15 pF	OE	Υ
	$\mathbf{t}_{\scriptscriptstyle ZL}$	_	20.5	36.0	1.0	38.0		C _L = 50 pF		
Disable time	t_{HZ}	_	8.3	20.0	1.0	22.5	ns	$C_L = 15 pF$	OE	Υ
	\mathbf{t}_{LZ}	_	13.0	29.5	1.0	32.0		C _L = 50 pF	_	

• $V_{CC} = 2.5 \pm 0.2 \text{ V}$

Item	Symbol	$T_a = 25^{\circ}C$		$T_a = -40 \text{ to } 85^{\circ}\text{C}$		Unit	Test	FROM	то	
		Min	Тур	Max	Min	Max	_	Conditions	(Input)	(Output)
Propagation	t _{PLH}	_	7.1	13.0	1.0	15.5	ns	C _L = 15 pF	Α	Υ
delay time	$t_{\tiny PHL}$	_	9.2	16.5	1.0	18.5	_	C _L = 50 pF	_	
Enable time	t _{zH}	_	7.4	13.0	1.0	15.5	ns	C _L = 15 pF	OE	Υ
	t_{ZL}	_	9.5	16.5	1.0	18.5	_	C _L = 50 pF	_	
Disable time	t _{HZ}	_	5.7	14.7	1.0	17.0	ns	C _L = 15 pF	OE	Υ
	\mathbf{t}_{LZ}	_	8.1	18.2	1.0	20.5	_	C _L = 50 pF	_	

• $V_{CC} = 3.3 \pm 0.3 \text{ V}$

Item	Symbol	$T_a = 25^{\circ}C$		$T_a = -40$ to 85° C		Unit	Test	FROM	то	
		Min	Тур	Max	Min	Max	_	Conditions	(Input)	(Output)
Propagation	t _{PLH}	_	5.0	8.0	1.0	9.5	ns	C _L = 15 pF	Α	Υ
delay time	$t_{\tiny PHL}$	_	6.4	11.5	1.0	13.0		C _L = 50 pF		
Enable time	t _{zH}	_	5.1	8.0	1.0	9.5	ns	C _L = 15 pF	OE	Υ
	$\mathbf{t}_{\scriptscriptstyleZL}$	_	6.6	11.5	1.0	13.0	_	C _L = 50 pF	_	
Disable time	t _{HZ}	_	4.4	9.7	1.0	11.5	ns	C _L = 15 pF	OE	Υ
	\mathbf{t}_{LZ}	_	6.1	13.2	1.0	15.0		C _L = 50 pF	_	

Switching Characteristics (cont)

•
$$V_{CC} = 5.0 \pm 0.5 V$$

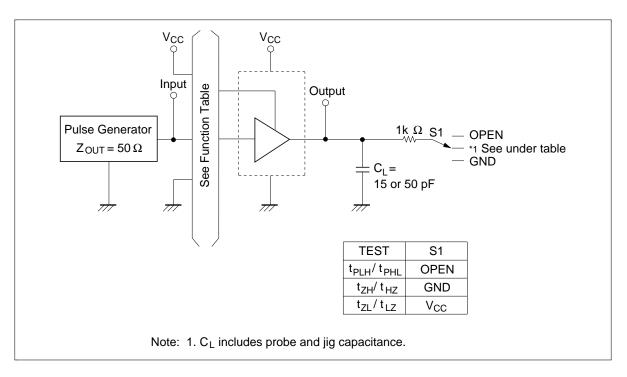
Item	Symbol	$T_a = 2$	$T_a = 25^{\circ}C$ $T_a = -40 \text{ to } 85^{\circ}C$		Unit	Test	FROM	то		
		Min	Тур	Max	Min	Max		Conditions	(Input)	(Output)
Propagation	t _{PLH}	_	3.5	5.5	1.0	6.5	ns	C _L = 15 pF	Α	Υ
delay time	$t_{\tiny PHL}$	_	4.6	7.5	1.0	8.5		C _L = 50 pF	_	
Enable time	t _{zH}	_	3.6	5.1	1.0	6.0	ns	C _L = 15 pF	OE	Υ
	t_{zL}	_	4.6	7.1	1.0	8.0		C _L = 50 pF	_	
Disable time	t _{HZ}	_	3.3	6.8	1.0	8.0	ns	C _L = 15 pF	OE	Υ
	t_{\scriptscriptstyleLZ}	_	4.3	8.8	1.0	10.0	_	C _L = 50 pF	_	

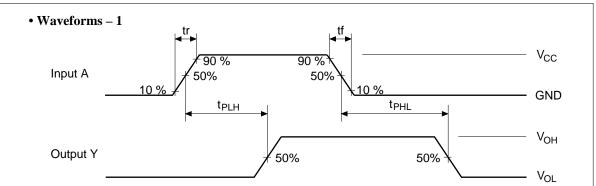
Operating Characteristics

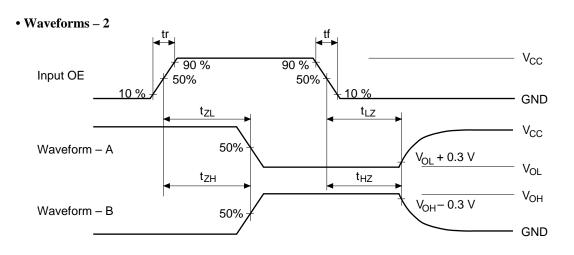
• $C_L = 50 pF$

Item	Symbol	V _{cc} (V)	$T_a = 25^{\circ}C$			Unit	Test Conditions
			Min	Тур	Max	<u> </u>	
Power dissipation capacitance	C_{PD}	3.3	_	10.5	_	pF	f = 10 MHz
		5.0	_	11.5	_		

Test Circuit





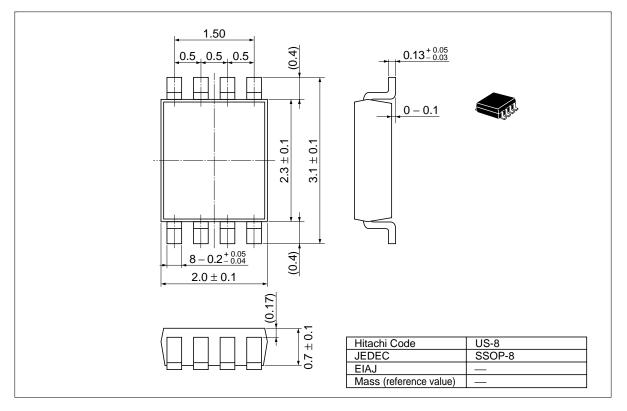


Notes: 1. $tr \le 3$ ns, $tf \le 3$ ns

- 2. Input waveform : PRR ≤ 1 MHz, duty cycle 50%
- 3. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 4. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.

Package Dimensions

Unit: mm



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Hitachi. Ltd.

Semiconductor & Integrated Circuits. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL

NorthAmerica http://semiconductor.hitachi.com/ Europe http://www.hitachi-eu.com/hel/ecq : http://www.hitachi.com.sg/grp3/sicd : http://www.hitachi.co.jp/Sicd/indx.htm Asia Japan

For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Germany

Hitachi Europe GmbH Electronic Components Group Dornacher Stra§e 3 D-85622 Feldkirchen, Munich

Fax: <1>(408) 433-0223 Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00

> Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead

Berkshire SL6 8YA, United Kingdom Tel: <886> (2) 2718-3666 Tel: <44> (1628) 585000 Fax: <44> (1628) 585160

Hitachi Asia I td 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533

Hitachi Asia Ltd. Taipei Branch Office 3rd Flr, Hung Kuo Building, No.167, Tun Hwa North Road, Taipei (105) Taiwan

Fax: <886> (2) 2718-8180 Telex: 23222 HAS-TP

Colophon 1.0

Hitachi Asia (Hong Kong) Ltd.

Kowloon, Hong Kong

Tel: <852> (2) 735 9218 Fax: <852> (2) 730 0281

Telex: 40815 HITEC HX

Group III (Electronic Components) 7th Flr, North Tower, World Finance Centre,

Harbour City, Canton Road, Tsim Sha Tsui,

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